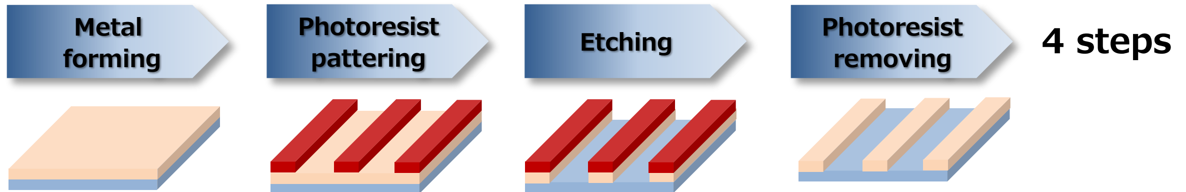
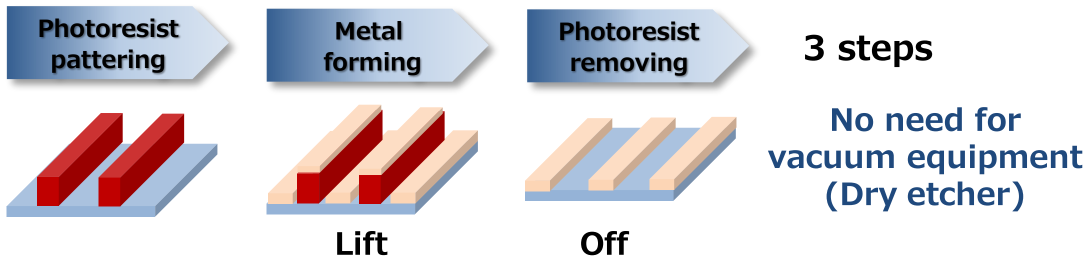
# NAGASE Photoresist for Lift-off Process

## Lift-off Process

### Etching process ( Conventional )



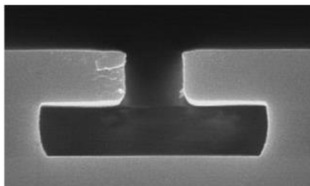

### Lift-off process




## Product by i-line stepper exposure (NA=0.45)

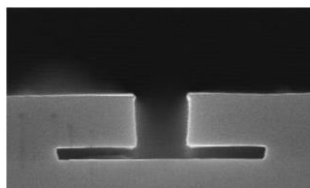
### Bi-layer type

**BLX series ( Under layer )**



Thickness
Upper layer : 1um
Under layer : 0.7um

0.5um trench pattern



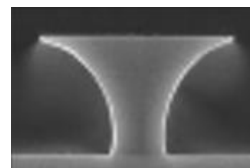
Thickness
Upper layer : 1um
Under layer : 0.2um

0.5um trench pattern

- No intermixing
- Applicable to various upper layer
- Selectable of exposure wavelength depending on upper layer

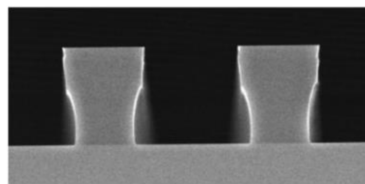
### Single-layer type

**NPR9700 series**



Thickness
10um

10um L/S pattern



Thickness
20um

10um L/S pattern

- Positive-tone type
- Simple process
- Good step coverage
- Suitable anti-tapered profile

**Customizable for customer needs**


Nagase ChemteX
NAGASE Group

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NAGASE & CO.,LTD.